



Form 1449 (Modified)	Atty Docket No. NOVLP088/NVLS-2882	Application No.: 10/825,888
Information Disclosure Statement By Applicant	Applicant: Bandyopadhyay et al.	
(Use Several Sheets if Necessary)	Filing Date April 16, 2004	Group 2891

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
JSKS	A1	6,867,086 B1	03.2005	Chen et al.			
	A2	6,903,004	06.2005	Spencer et al.			
	A3	6,232,658 B1	05.2001	Catabay et al.			
	A4	6,171,661	01.2001	Zheng et al.			
	A5	2002/0016085	02.2002	Huang et al.			
	A6	6,455,417	09.2002	Bao et al.			
	A7	7,018,918	03.2006	Kloster et al.			
	A8	6,849,549	02.2005	Chiou et al.			
	A9	2002/0141024 A1	10.2002	Retschke et al.			
	A10	2002/0064341 A1	05.2002	Fauver et al.			
	A11	7,094,713 B1	08.22.06	Niu et al.			
	A12	6,306,564	10.2001	Mullee, William H.			
	A13	2003/0066544 A1	04.2003	Jur et al.			
	A14	6,149,828 A	11.2000	Vaartstra, Brian A.			
	A15	6,943,121 B2	09.2005	Leu et al.			
	A16	2004/0102032 A1	05.2004	Kloster et al.			
	A17	2006/0110931 A1	05.2006	Fukazawa et al.			
✓	A18	7,087,271 B2	08.2006	Rhee et al.			

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
JSKS  ↓  ✓	C1	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/941,502 [Atty Dkt No. NOVLP107/NVLS-2932].
	C2	U.S. Office Action mailed May 30, 2006, from U.S Application No. 10/785,235 [Atty Dkt No. NOVLP085/NVLS-2875].
	C3	U.S. Office Action mailed May 31, 2006, from U.S Application No. 10/849,568 [Atty Dkt No. NOVLP083/NVLS-2867].
	C4	U.S. Office Action mailed May 2, 2006, from U.S Application No. 11/050,621 [Atty Dkt No. NOVLP100/NVLS-2956].
	C5	U.S. Office Action mailed June 15, 2006, from U.S Application No. 10/800,409 [Atty Dkt No. NOVLP098/NVLS-2907].
	C6	Kelman et al., "Method for Reducing Stress in Porous Dielectric Films", U.S. Application No. 11/369,311, filed March 6, 2006 (Atty Dkt: NOVLP154/NVLS-3121)
Examiner	Date Considered	


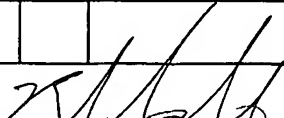
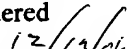
Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	April 16, 2004	2891

**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub- class	Filing Date

**Other Documents**

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
JKS 	C7	U.S. Office Action mailed May 2, 2006, from U.S Application No. 10/295,965.
	C8	U.S. Office Action mailed August 9, 2005, from U.S Application No. 10/295,965.
	C9	U.S. Office Action mailed June 14, 2006, from U.S Application No. 10/789,103 [Atty Dkt No. NOVLP094/NVLS-2919].
	C10	U.S. Office Action mailed September 8, 2006, from U.S Application No. 10/404,693 [Atty Dkt No. NOVLP064/NVLS-794].
	C11	U.S. Office Action mailed September 7, 2006, from U.S Application No. 10/820,525 [Atty Dkt No. NOVLP091/NVLS-2889].
	C12	U.S. Office Action mailed July 12, 2006, from U.S Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
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	Date Considered	

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#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
JSKS	A1	2006/0197881	09.2006	Kang et al.			
JSKS	A2	6,331,480	12.2001	Tsai et al.			

#### Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
JSKS	C1	U.S. Office Action mailed May 2, 2006, from U.S. Application No. 10/295,965.
	C2	U.S. Office Action mailed August 9, 2005, from U.S. Application No. 10/295,965.
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	C6	U.S. Office Action mailed July 12, 2006, from U.S. Application No. 10/672,305 [Atty Dkt No. NOVLP069/NVLS-2821].
	C7	Wu et al., "Methods for Fabricating High Hardness/Modules Low Dielectric Constant Materials," Novellus Systems, Inc., Appln No. 11/369,658, filed March 6, 2006, pp. 1-33. [NOVLP148/NVLS-3111]
	C8	Dhas et al., "Method of Reducing Defects in PECVD TEOS Films," Novellus Systems, Inc., Appln No. 11/396,303, filed March 30, 2006, pp. 1-21. [NOVLP160/NVLS-3168]
Examiner	Date Considered 12/19/06	

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